

## KSC5042

### **High Voltage Switching Dynamic Focus Application**

- High Collector-Emitter Breakdown Voltage : BV<sub>CEO</sub>=900V
- Small C<sub>ob</sub> =2.8pF(Typ.)
  Wide S.O.A
- High reliability



1.Base 2.Collector 3.Emitter

## **NPN Triple Diffused Planar Silicon Transistor**

### Absolute Maximum Ratings T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	1500	V
$V_{CEO}$	Collector-Emitter Voltage	900	V
$V_{EBO}$	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current (DC)	100	mA
I <sub>CP</sub>	Collector Current (Pulse)	300	mA
P <sub>C</sub>	Collector Dissipation (T <sub>C</sub> =25°C)	10	W
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	- 55 ~ 150	°C

### Electrical Characteristics T<sub>C</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=1 \text{ mA}, I_{E}=0$	1500			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	$I_{C}=5mA, I_{B}=0$	900			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	$I_E=1$ mA, $I_C=0$	5			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB} = 900V, I_{E} = 0$			10	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB} = 4V, I_C = 0$			10	μΑ
h <sub>FE</sub>	*DC Current Gain	$V_{CE}=5V$ , $I_{C}=10mA$	30			
V <sub>CE</sub> (sat)	*Collector-Emitter Saturation Voltage	$I_C=20$ mA, $I_B=4$ mA			5	V
V <sub>BE</sub> (sat)	*Base-Emitter Saturation Voltage	$I_C=20$ mA, $I_B=4$ mA			2	V
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =100V, f = 1MHz		2.8		pF

<sup>\*</sup> Pulse test: PW = 300μs, Duty Cycle = 2% pulsed

# **Typical Characteristics**

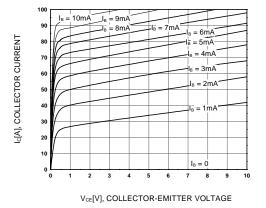


Figure 1. Static Characteristic

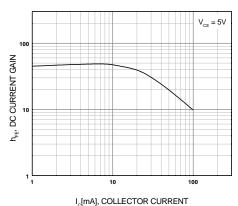


Figure 2. DC current Gain

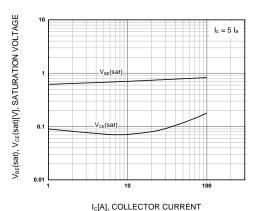


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

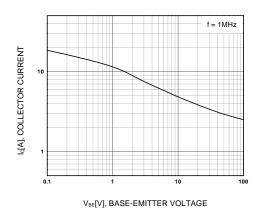


Figure 4. Collector Output Capacitance

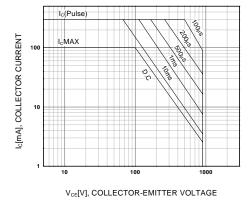


Figure 5. Safe Operating Area

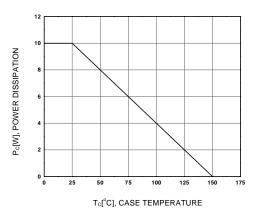
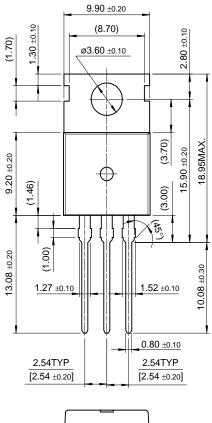


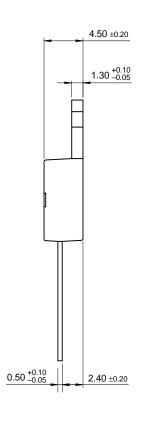
Figure 6. Power Derating

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# **Package Demensions**

# TO-220





10.00 ±0.20

Dimensions in Millimeters

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